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ADD-A-PAK Generation VII Power Modules Thyristor/Thyristor, 95 A



ADD-A-PAK

PRODUCT SUMMARY					
I _{T(AV)}	95 A				

MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package
- · Low thermal resistance
- UL approved file E78996 😱
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

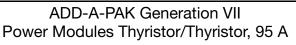
ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I _{T(AV)}	85 °C	95						
I _{T(RMS)}		150	A					
I _{TSM}	50 Hz	z 2000						
	60 Hz	2094						
l ² t	50 Hz	20	kA ² s					
1-1	60 Hz	18.26	KA-S					
l²√t		200	kA²√s					
V _{RRM}	Range	400 to 1600	V					
T _{Stg}		- 40 to 125	°C					
TJ		- 40 10 125	C					



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA			
	04	400	500	400				
VSK.91	08	800	900	800	15			
12		1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION			TEST COND			
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	180° conductic T _C = 85 °C	180° conduction, half sine wave, $T_{\rm C} = 85\ ^{\circ}{\rm C}$		95	A
Maximum continuous RMS on-state current		DC			150	
Maximum continuous RMS on-state current	I _{T(RMS)}	T _C			78	°C
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	2094	•
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	half wave, initial T _J = T _J maximum	1682	A
		t = 8.3 ms	reapplied		1760	
		t = 10 ms	No voltage		20	kA ² s
	l ² t	t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	18.26	
Maximum I ² t for fusing		t = 10 ms	100 % V _{BBM}		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I ² \sqrt{t} for fusing	l²√t (1)	t = 0.1 ms to 1 T _J = T _J maximu	200	kA²√s		
	V _{T(TO)} ⁽²⁾	Low level ⁽³⁾			0.97	
Maximum value of threshold voltage		High level ⁽⁴⁾	$T_J = T_J maxin$	num	1.1	V
Maximum value of on-state	(2)	Low level ⁽³⁾			2.76	
slope resistance	r _t ⁽²⁾	High level ⁽⁴⁾	$T_J = T_J maxin$	num	2.38	mΩ
Maximum on-state voltage drop	V _{TM}	$I_{TM} = \pi \times I_{T(AV)}$	T _J = 25 °C		1.73	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25 \text{ °C, from}$ $I_{TM} = \pi \times I_{T(AV)},$	150	A/µs		
Maximum holding current	Ι _Η	T _J = 25 °C, and resistive load, g	250	mA		
Maximum latching current	١ _L	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400	

Notes

⁽¹⁾ I²t for time $t_x = I^2 \sqrt{t} x \sqrt{t_x}$

(2) Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ (3) 16.7 % x $\pi \times I_{AV} < I < \pi \times I_{AV}$

(4) $I > \pi \times I_{AV}$



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TRIGGERING							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}			12	W		
Maximum average gate power	P _{G(AV)}			3.0	vv		
Maximum peak gate current	I _{GM}			3.0	А		
Maximum peak negative gate voltage	m peak negative gate voltage - V _{GM}			10			
	V _{GT}	T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V		
Maximum gate voltage required to trigger		T _J = 25 °C		2.5			
		T _J = 125 °C		1.7			
		T _J = - 40 °C		270			
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	mA		
		T _J = 125 °C		80			
Maximum gate voltage that will not trigger	V _{GD}	$T_J = 125 \text{ °C}, \text{ rated } V_{DRI}$	_M applied	0.25	V		
Maximum gate current that will not trigger	I _{GD}	$T_J = 125 \ ^\circ C$, rated V_{DRI}	6	mA			

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS		
Junction operating and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C		
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.22	°C/W		
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1			
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm		
	busbar		3 hours to allow for the spread of the compound.	3	NIII		
Approximate weight				75	g		
				2.7	oz.		
Case style			JEDEC	TO-240AA	compatible		

DEVICES	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION					
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSK.91	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

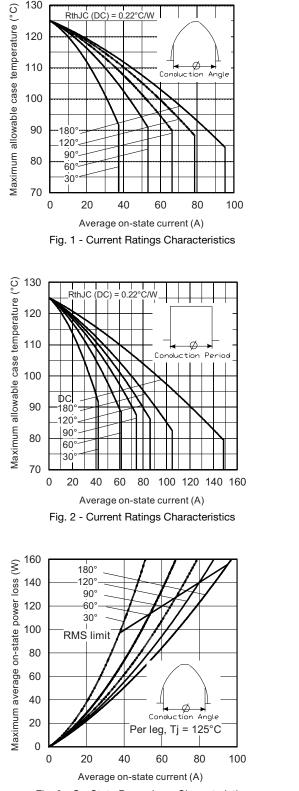
Note

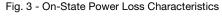
Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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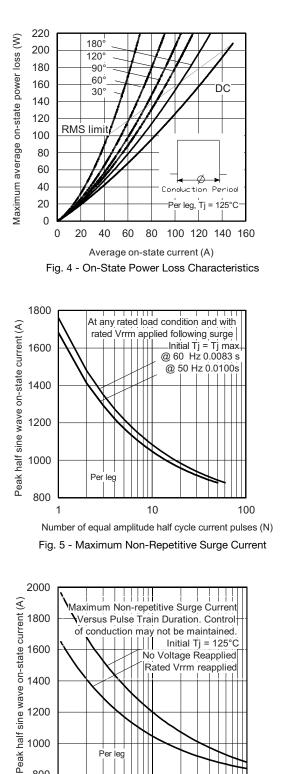


Fig. 6 - Maximum Non-Repetitive Surge Current

Pulse train duration (s)

0.1

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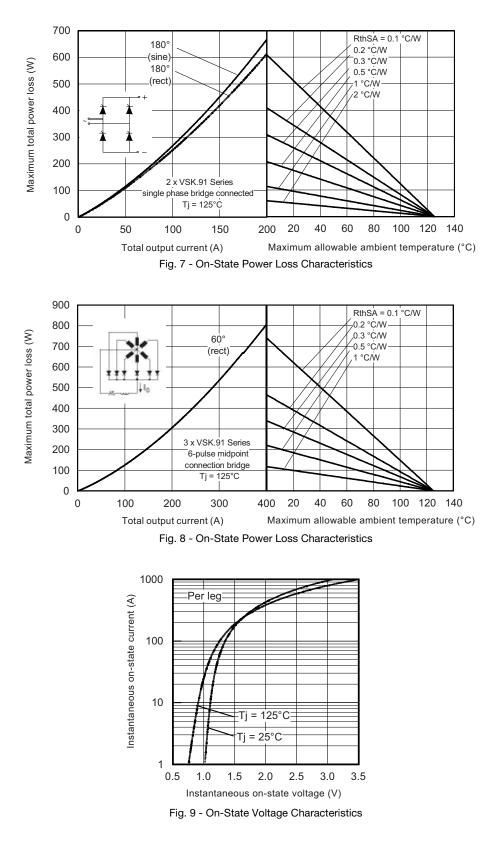
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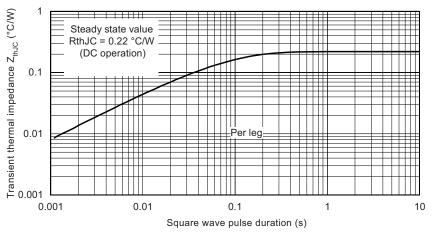
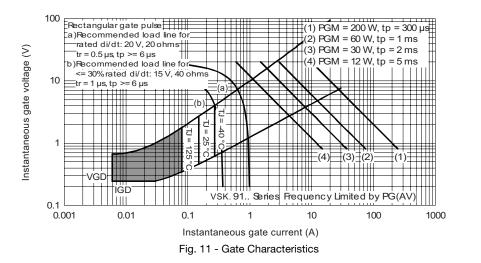
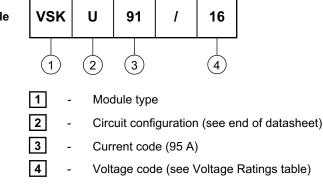


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



Note

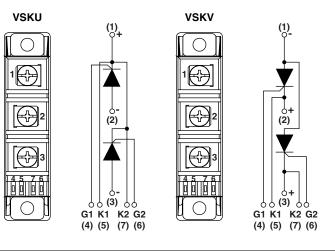
• To order the optional hardware go to www.vishay.com/doc?95172

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CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



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